

Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Ξ·ΧϜΙ

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	15
Program Memory Size	48KB (48K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	3K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 6x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	25-WFLGA
Supplier Device Package	25-LGA (3x3)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f1008dala-w0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

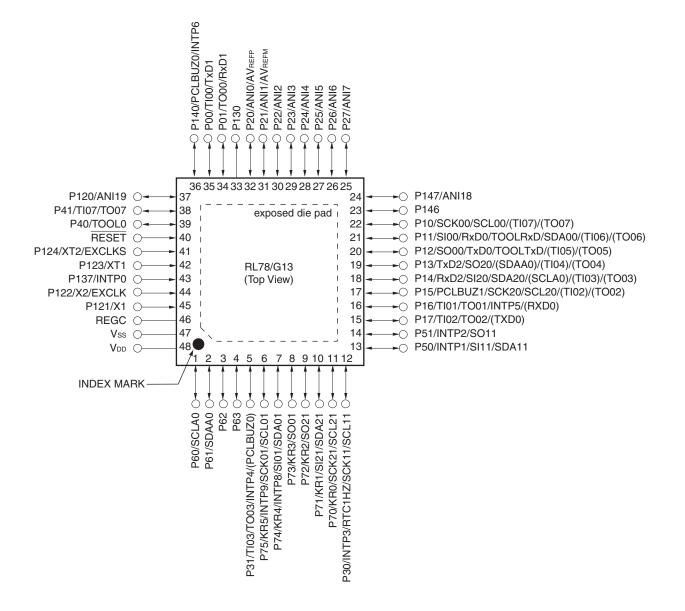
	1	1	T	(7/12)
Pin count	Package	Data flash	Fields of Application	Ordering Part Number
52 pins	52-pin plastic LQFP (10 × 10	Mounted	A	R5F100JCAFA#V0, R5F100JDAFA#V0, R5F100JEAFA#V0, R5F100JFAFA#V0, R5F100JGAFA#V0, R5F100JHAFA#V0,
	mm, 0.65 mm			R5F100JJAFA#V0, R5F100JKAFA#V0, R5F100JLAFA#V0
	pitch)			R5F100JCAFA#X0, R5F100JDAFA#X0, R5F100JEAFA#X0,
				R5F100JFAFA#X0, R5F100JGAFA#X0, R5F100JHAFA#X0,
				R5F100JJAFA#X0, R5F100JKAFA#X0, R5F100JLAFA#X0
			D	R5F100JCDFA#V0, R5F100JDDFA#V0, R5F100JEDFA#V0,
				R5F100JFDFA#V0, R5F100JGDFA#V0, R5F100JHDFA#V0,
				R5F100JJDFA#V0, R5F100JKDFA#V0, R5F100JLDFA#V0
				R5F100JCDFA#X0, R5F100JDDFA#X0, R5F100JEDFA#X0,
				R5F100JFDFA#X0, R5F100JGDFA#X0, R5F100JHDFA#X0,
				R5F100JJDFA#X0, R5F100JKDFA#X0, R5F100JLDFA#X0
			G	R5F100JCGFA#V0, R5F100JDGFA#V0, R5F100JEGFA#V0,
				R5F100JFGFA#V0,R5F100JGGFA#V0,R5F100JHGFA#V0,
				R5F100JJGFA#V0
				R5F100JCGFA#X0, R5F100JDGFA#X0, R5F100JEGFA#X0,
				R5F100JFGFA#X0,R5F100JGGFA#X0, R5F100JHGFA#X0,
				R5F100JJGFA#X0
		Not	А	R5F101JCAFA#V0, R5F101JDAFA#V0, R5F101JEAFA#V0,
		mounted		R5F101JFAFA#V0, R5F101JGAFA#V0, R5F101JHAFA#V0,
				R5F101JJAFA#V0, R5F101JKAFA#V0, R5F101JLAFA#V0
				R5F101JCAFA#X0, R5F101JDAFA#X0, R5F101JEAFA#X0,
				R5F101JFAFA#X0, R5F101JGAFA#X0, R5F101JHAFA#X0,
				R5F101JJAFA#X0, R5F101JKAFA#X0, R5F101JLAFA#X0
			D	R5F101JCDFA#V0, R5F101JDDFA#V0, R5F101JEDFA#V0,
				R5F101JFDFA#V0, R5F101JGDFA#V0, R5F101JHDFA#V0,
				R5F101JJDFA#V0, R5F101JKDFA#V0, R5F101JLDFA#V0
				R5F101JCDFA#X0, R5F101JDDFA#X0, R5F101JEDFA#X0,
				R5F101JFDFA#X0, R5F101JGDFA#X0, R5F101JHDFA#X0,
				R5F101JJDFA#X0, R5F101JKDFA#X0, R5F101JLDFA#X0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



• 48-pin plastic HWQFN (7 × 7 mm, 0.5 mm pitch)



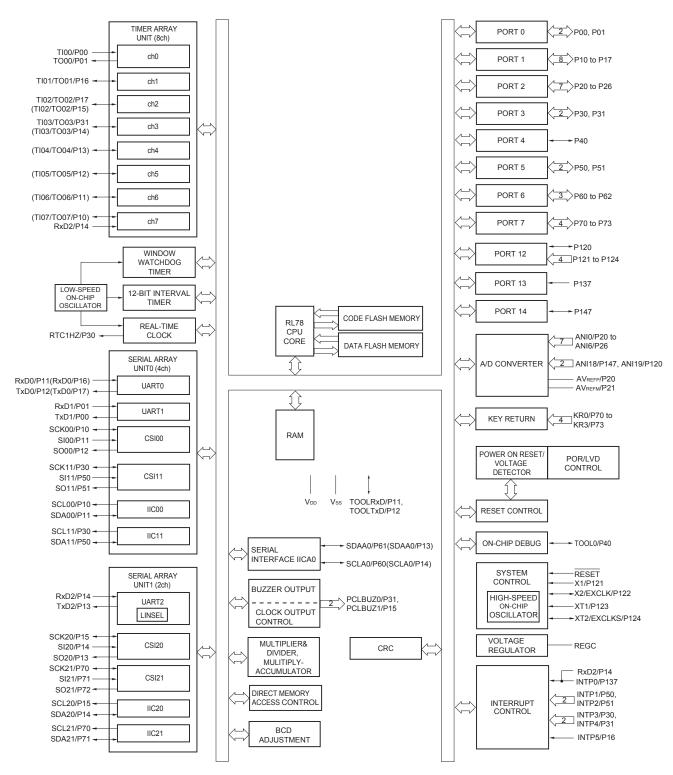
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.
- 3. It is recommended to connect an exposed die pad to $V_{\mbox{\scriptsize ss.}}$



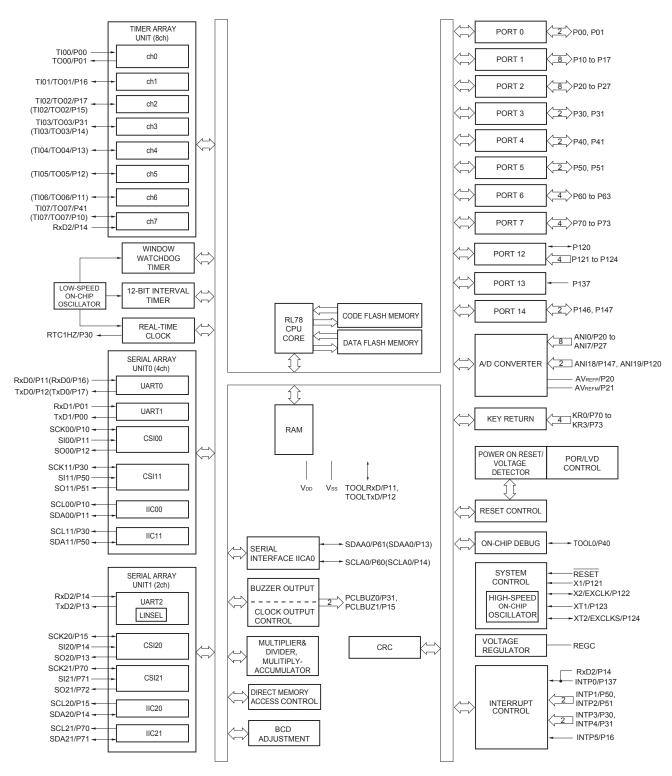
1.5.7 40-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.



1.5.8 44-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register** (**PIOR**) in the RL78/G13 User's Manual.



 The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see 6.9.3 Operation as multiple PWM output function in the RL78/G13 User's Manual).

^{3.} When setting to PIOR = 1

lt a	m	40-pin 44-pin 48-pin				EO	nin	(2/2) 64-pin			
Ite					İ.			52	-pin I		
		R5F100Ex	R5F101Ex	R5F100Fx	R5F101Fx	R5F100Gx	R5F101Gx	R5F100Jx	R5F101Jx	R5F100Lx	R5F101Lx
Clock output/buzz	er output	:	2		2		2		2		2
·		 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: fMAIN = 20 MHz operation) 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: fsub = 32.768 kHz operation) 									
8/10-bit resolution	A/D converter	9 channe	ls	10 chanr	nels	10 chanr	nels	12 chan	nels	12 chanr	nels
Serial interface		[40-pin, 4	4-pin prod	ducts]		J				J	
		 CSI: 1 CSI: 2 [48-pin, 5 CSI: 2 CSI: 1 CSI: 2 [64-pin pineter of the second sec	 CSI: 1 channel/simplified I²C: 1 channel/UART: 1 channel CSI: 1 channel/simplified I²C: 1 channel/UART: 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART (UART supporting LIN-bus): 1 channel [48-pin, 52-pin products] CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel CSI: 1 channel/simplified I²C: 1 channel/UART: 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART (UART supporting LIN-bus): 1 channel [64-pin products] CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel 								
	I ² C bus	1 channe		1 channe		1 channe		1 channe		1 channe	
Multiplier and divid		 I chainer i chainer i chainer i chainer i chainer I bits × 16 bits = 32 bits (Unsigned or signed) 32 bits ÷ 32 bits = 32 bits (Unsigned) 									
		16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed)									
DMA controller		2 channe	ls								
Vectored	Internal	2	27	:	27	2	27		27	2	27
interrupt sources	External		7		7		10		12		13
Key interrupt			4		4		6		8		8
Reset		 Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution ^{Note} Internal reset by RAM parity error Internal reset by illegal-memory access 									
Power-on-reset ci	rcuit	 Power-on-reset: 1.51 V (TYP.) Power-down-reset: 1.50 V (TYP.) 									
Voltage detector		• Rising edge : 1.67 V to 4.06 V (14 stages) • Falling edge : 1.63 V to 3.98 V (14 stages)									
On-chip debug fur	nction	Provided									
Power supply volta				$T_A = -40$ to $T_A = -40$ to							
Operating ambien	t temperature	$V_{DD} = 2.4$ to 5.5 V (T _A = -40 to +105°C) T _A = 40 to +85°C (A: Consumer applications, D: Industrial applications) T _A = 40 to +105°C (G: Industrial applications)									

<R>

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.



2.1 Absolute Maximum Ratings

Absolute Maximum Ratings ($T_A = 25^{\circ}C$) ((1/2)	
--	-------	--

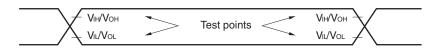
Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	VDD		–0.5 to +6.5	V
	EVDD0, EVDD1	EVDD0 = EVDD1	–0.5 to +6.5	V
	EVsso, EVss1	EVsso = EVss1	–0.5 to +0.3	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8 and -0.3 to V _{DD} +0.3 ^{Note 1}	V
Input voltage	VII	P00 to P07, P10 to P17, P30 to P37, P40 to P47,	-0.3 to EVDD0 +0.3	V
		P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	and –0.3 to V _{DD} +0.3 ^{Note 2}	
	VI2	P60 to P63 (N-ch open-drain)	–0.3 to +6.5	V
	Vı3	P20 to P27, P121 to P124, P137, P150 to P156, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Output voltage	Voi	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147		V
	V ₀₂	P20 to P27, P150 to P156	-0.3 to VDD +0.3 Note 2	V
Analog input voltage	VAI1	ANI16 to ANI26	-0.3 to EV _{DD0} +0.3 and -0.3 to AV _{REF} (+) +0.3 ^{Notes 2, 3}	V
	Vai2	ANI0 to ANI14	-0.3 to V_DD +0.3 and -0.3 to AV_REF(+) +0.3 Notes2,3	V

- **Notes 1.** Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - **3.** Do not exceed $AV_{REF}(+) + 0.3 V$ in case of A/D conversion target pin.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - **2.** $AV_{REF}(+)$: + side reference voltage of the A/D converter.
 - 3. Vss : Reference voltage



2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit

(1) During communication at same potential (UART mode) (TA = -40 to +85°C, 1.6 V \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 V, Vss = EV_{ss0} = EV_{ss1} = 0 V)

Parameter	Symbol		Conditions H		h-speed Mode	``	/-speed Mode	``	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate Note 1		2.4 V≤ EV	5.5 V		fMCK/6 Note 2		fмск/6		fмск/6	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 3}$		5.3		1.3		0.6	Mbps
		1.8 V ≤ EV	$T_{\text{DD0}} \leq 5.5 \text{ V}$		fмск/6 Note 2		fмск/6		fмск/6	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 3}$		5.3		1.3		0.6	Mbps
		1.7 V ≤ EV	$T_{\text{DD0}} \leq 5.5 \text{ V}$		fMCK/6 Note 2		fмск/6 Note 2		fмск/6	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 3}$		5.3		1.3		0.6	Mbps
		1.6 V ≤ EV	$T_{\text{DD0}} \leq 5.5 \text{ V}$	_	_		fмск/6 Note 2		fмск/6	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 3}$	_	_		1.3		0.6	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The following conditions are required for low voltage interface when $E_{VDD0} < V_{DD}$.

 $2.4~V \leq EV_{\text{DD0}}$ < 2.7 V : MAX. 2.6 Mbps

- $1.8~\text{V} \leq \text{EV}_\text{DD0} < 2.4~\text{V}$: MAX. 1.3 Mbps
- $1.6~V \leq EV_{\text{DD0}} < 1.8~V$: MAX. 0.6 Mbps
- 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are:

 $\begin{array}{lll} \text{HS (high-speed main) mode:} & 32 \ \text{MHz} \ (2.7 \ \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \ \text{V}) \\ & 16 \ \text{MHz} \ (2.4 \ \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \ \text{V}) \\ \text{LS (low-speed main) mode:} & 8 \ \text{MHz} \ (1.8 \ \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \ \text{V}) \\ \text{LV (low-voltage main) mode:} & 4 \ \text{MHz} \ (1.6 \ \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \ \text{V}) \\ \end{array}$

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).



Parameter	Symbo I		Conditions	HS (higl main)		LS (low-sp Mo	eed main) de) LV (low-voltage main) Mode			
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
SIp setup time (to SCKp↑) ^{Note 1}	tsik2	2.7 V ≤ E	$EV_{DD0} \leq 5.5 V$	1/fмск+2 0		1/fмск+30		1/fмск+30		ns	
		1.8 V ≤ E	$EV_{DD0} \leq 5.5 \text{ V}$	1/fмск+3 0		1/fмск+30		1/fмск+30		ns	
		1.7 V ≤ E	$EV_{DD0} \leq 5.5 \text{ V}$	1/fмск+4 0		1/fмск+40		1/fмск+40		ns	
		1.6 V ≤	$EV_{DD0} \leq 5.5 V$			1/fмск+40		1/fмск+40		ns	
SIp hold time (from SCKp↑)	tksi2	1.8 V ≤ E	$8~V \leq EV_{\text{DD0}} \leq 5.5~V$			1/fмск+31		1/fмск+31		ns	
Note 2		1.7 V ≤ E	$EV_{DD0} \leq 5.5 \text{ V}$	1/fмск+ 250		1/fмск+ 250		1/fмск+ 250		ns	
		1.6 V ≤	$EV_{DD0} \leq 5.5 V$	—		1/fмск+ 250		1/fмск+ 250		ns	
Delay time from SCKp↓ to	tkso2	C = 30 pF ^{Note 4}	$\begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} \leq 5.5 \\ V \end{array}$		2/f _{мск+} 44		2/f _{мск+} 110		2/f _{мск+} 110	ns	
SOp output Note 3			$\begin{array}{l} 2.4 \ V \leq EV_{\text{DD0}} \leq 5.5 \\ V \end{array}$		2/fмск+ 75		2/fмск+ 110		2/fмск+ 110	ns	
			$\begin{array}{l} 1.8 \ V \leq EV_{\text{DD0}} \leq 5.5 \\ V \end{array}$		2/fмск+ 110		2/fмск+ 110		2/fмск+ 110	ns	
			$\begin{array}{l} 1.7 \ V \leq EV_{\text{DD0}} \leq 5.5 \\ V \end{array}$		2/fмск+ 220		2/fмск+ 220		2/fмск+ 220	ns	
			$\begin{array}{l} 1.6 \ V \leq EV_{\text{DD0}} \leq 5.5 \\ V \end{array}$		_		2/fмск+ 220		2/fмск+ 220	ns	

(4)	During communication at same potential (CSI mode) (slave mode, SCKp external clock input) (2/2)
	$(T_A = -40 \text{ to } \pm 85^{\circ}\text{C} = 1.6 \text{ V} \leq \text{EV}_{DD0} = \text{EV}_{DD1} \leq \text{V}_{DD1} \leq 5.5 \text{ V}_{D0} \text{ V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0.0 \text{ V}_{D1}$

- Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

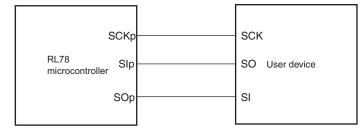
Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 4, 5, 8, 14)

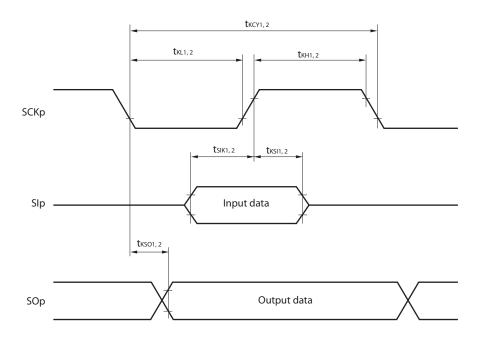
fMCK: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))



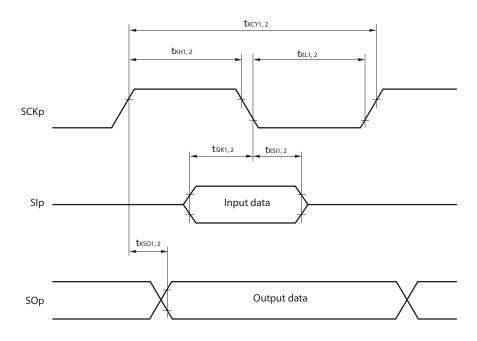
CSI mode connection diagram (during communication at same potential)

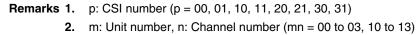


CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)







Parameter	Symbol		Conditions		speed	high- main) ode		/-speed Mode	voltage	low- e main) ode	Unit
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Recep- tion	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V \end{array}$			fмск/6 Note 1		fмск/6 Note 1		fмск/6 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 4}$		5.3		1.3		0.6	Mbps
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$			fмск/6 Note 1		fмск/6 Note 1		fмск/6 Note 1	bps
				Theoretical value of the maximum transfer rate fмск = fclк ^{Note 4}		5.3		1.3		0.6	Mbps
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$			fMCK/6 Notes 1 to 3		fMCK/6 Notes 1, 2		fMCK/6 Notes 1, 2	bps
				Theoretical value of the maximum transfer rate fмск = fclк ^{Note 4}		5.3		1.3		0.6	Mbps

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2) (T_A = -40 to +85°C. 1.8 V \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 V. Vss = EV_{SS0} = EV_{SS1} = 0 V)

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

- **2.** Use it with $EV_{DD0} \ge V_b$.
- 3. The following conditions are required for low voltage interface when $E_{VDD0} < V_{DD}$.

 $2.4~V \leq EV_{\text{DD0}} < 2.7~V$: MAX. 2.6 Mbps

 $1.8~V \leq EV_{\text{DD0}} < 2.4~V$: MAX. 1.3 Mbps

4. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are: HS (high-speed main) mode: $32 \text{ MHz} (2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V})$

	16 MHz (2.4 V \leq VDD \leq 5.5 V)
LS (low-speed main) mode:	8 MHz (1.8 V \leq V_{DD} \leq 5.5 V)

LV (low-voltage main) mode: $4 \text{ MHz} (1.6 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V})$

- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- **Remarks 1.** $V_{b}[V]$: Communication line voltage
 - **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 - 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13)

4. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.



			$\sqrt{DD0} = EVDD1 \le VDD \le$						1.177	1	Lint
Parameter	Symbol		Conditions			high-		low-		low-	Unit
						main) ode	speed	main) ode		age Mode	
								1			
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Transmission	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$			Note		Note		Note	bps
			$2.7 \text{ V} \leq V_b \leq 4.0 \text{ V}$			1		1		1	
				Theoretical		2.8		2.8		2.8	Mbps
				value of the		Note 2		Note 2		Note 2	
				maximum							
				transfer rate							
				C _b = 50 pF, R _b =							
				$1.4 \text{ k}\Omega, V_{\text{b}} = 2.7$							
				V							
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$			Note		Note		Note	bps
			$2.3~V \leq V_b \leq 2.7~V$			3		3		3	
				Theoretical		1.2		1.2		1.2	Mbps
				value of the		Note 4		Note 4		Note 4	
				maximum							
				transfer rate							
				$C_b = 50 \text{ pF}, R_b =$							
				$2.7 \text{ k}\Omega$, V _b = 2.3							
				V							
			$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V},$			Notes		Notes		Notes	bps
			$1.6~V \leq V_b \leq 2.0~V$			5, 6		5, 6		5, 6	
				Theoretical		0.43		0.43		0.43	Mbps
				value of the		Note 7		Note 7		Note 7	
				maximum							
				transfer rate							
				$C_b = 50 \text{ pF}, R_b =$							
				$5.5 \text{ k}\Omega, \text{V}_{\text{b}} = 1.6$							
				V							

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2) (TA = -40 to +85°C, 1.8 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Notes 1. The smaller maximum transfer rate derived by using fMck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq EV $_{DD0} \leq$ 5.5 V and 2.7 V \leq V $_{b} \leq$ 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.



3. The smaller maximum transfer rate derived by using fMck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq EV_{DD0} < 4.0 V and 2.3 V \leq V_b \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) = $\frac{\frac{1}{|\text{Transfer rate} \times 2|} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{|\text{Transfer rate}|}) \times \text{Number of transferred bits}} \times 100 [\%]$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.
- $\textbf{5.} \quad \textbf{Use it with } EV_{DD0} \geq V_{b}.$
- 6. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate.

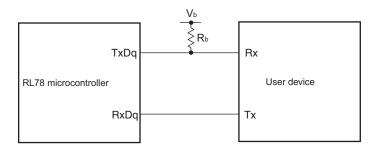
Expression for calculating the transfer rate when 1.8 V \leq EV_{DD0} < 3.3 V and 1.6 V \leq V_b \leq 2.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) = $\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **7.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 6 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)





2.6.2 Temperature sensor/internal reference voltage characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, $T_A = +25^{\circ}C$		1.05		V
Internal reference voltage	VBGR	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	Fvtmps	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μs

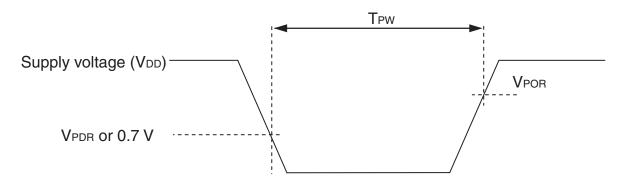
(TA = -40 to +85°C, 2.4 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V, HS (high-speed main) mode)

2.6.3 POR circuit characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	Power supply rise time	1.47	1.51	1.55	V
	VPDR	Power supply fall time	1.46	1.50	1.54	V
Minimum pulse width ^{Note}	Tpw		300			μS

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).





2.8 Flash Memory Programming Characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fclк	$1.8~V \leq V_{DD} \leq 5.5~V$	1		32	MHz
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years TA = 85°C	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 years Ta = 25°C		1,000,000		
		Retained for 5 years TA = 85°C	100,000			
		Retained for 20 years TA = 85°C	10,000			

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite.

The retaining years are until next rewrite after the rewrite.

- 2. When using flash memory programmer and Renesas Electronics self programming library
- **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

$(T_{\text{A}} = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \leq \text{EV}_{\text{DD}} = \text{EV}_{\text{DD}} \leq 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps



3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS $T_A = -40$ to +105°C)

This chapter describes the following electrical specifications.

Target products G: Industrial applications $T_A = -40$ to $+105^{\circ}C$ R5F100xxGxx

- Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. With products not provided with an EVDD0, EVDD1, EVSS0, or EVSS1 pin, replace EVDD0 and EVDD1 with VDD, or replace EVSS0 and EVSS1 with VSS.
 - 3. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 Functions for each product.
 - 4. Please contact Renesas Electronics sales office for derating of operation under $T_A = +85^{\circ}C$ to +105°C. Derating is the systematic reduction of load for the sake of improved reliability.

Remark When RL78/G13 is used in the range of $T_A = -40$ to +85°C, see **CHAPTER 2 ELECTRICAL SPECIFICATIONS (T_A = -40 to +85°C)**.

There are following differences between the products "G: Industrial applications ($T_A = -40$ to $+105^{\circ}C$)" and the products "A: Consumer applications, and D: Industrial applications".

Parameter	Ap	pplication
	A: Consumer applications, D: Industrial applications	G: Industrial applications
Operating ambient temperature	T _A = -40 to +85°C	T _A = -40 to +105°C
Operating mode Operating voltage range	$\begin{array}{l} \text{HS (high-speed main) mode:} \\ \text{2.7 V} \leq V_{\text{DD}} \leq 5.5 \ \text{V@1 MHz to 32 MHz} \\ \text{2.4 V} \leq V_{\text{DD}} \leq 5.5 \ \text{V@1 MHz to 16 MHz} \\ \text{LS (low-speed main) mode:} \\ \text{1.8 V} \leq V_{\text{DD}} \leq 5.5 \ \text{V@1 MHz to 8 MHz} \\ \text{LV (low-voltage main) mode:} \\ \text{1.6 V} \leq V_{\text{DD}} \leq 5.5 \ \text{V@1 MHz to 4 MHz} \end{array}$	HS (high-speed main) mode only: 2.7 V \leq V _{DD} \leq 5.5 V@1 MHz to 32 MHz 2.4 V \leq V _{DD} \leq 5.5 V@1 MHz to 16 MHz
High-speed on-chip oscillator clock accuracy	$\begin{array}{l} 1.8 \ V \leq V_{DD} \leq 5.5 \ V \\ \pm 1.0\% @ \ T_{A} = -20 \ to \ +85^{\circ}C \\ \pm 1.5\% @ \ T_{A} = -40 \ to \ -20^{\circ}C \\ 1.6 \ V \leq V_{DD} < 1.8 \ V \\ \pm 5.0\% @ \ T_{A} = -20 \ to \ +85^{\circ}C \\ \pm 5.5\% @ \ T_{A} = -40 \ to \ -20^{\circ}C \end{array}$	$\begin{array}{l} 2.4 \ V \leq V_{DD} \leq 5.5 \ V \\ \pm 2.0\% @ \ T_{A} = +85 \ to \ +105^{\circ}C \\ \pm 1.0\% @ \ T_{A} = -20 \ to \ +85^{\circ}C \\ \pm 1.5\% @ \ T_{A} = -40 \ to \ -20^{\circ}C \end{array}$
Serial array unit	UART CSI: fcLk/2 (supporting 16 Mbps), fcLk/4 Simplified I ² C communication	UART CSI: fcLK/4 Simplified I ² C communication
IICA	Normal mode Fast mode Fast mode plus	Normal mode Fast mode
Voltage detector	Rise detection voltage: 1.67 V to 4.06 V (14 levels) Fall detection voltage: 1.63 V to 3.98 V (14 levels)	Rise detection voltage: 2.61 V to 4.06 V (8 levels) Fall detection voltage: 2.55 V to 3.98 V (8 levels)

(Remark is listed on the next page.)



- Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter is in operation.
- 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- 8. Current flowing only during data flash rewrite.
- **9.** Current flowing only during self programming.
- 10. For shift time to the SNOOZE mode, see 18.3.3 SNOOZE mode in the RL78/G13 User's Manual.

Remarks 1. fil: Low-speed on-chip oscillator clock frequency

- 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- 3. fclk: CPU/peripheral hardware clock frequency
- 4. Temperature condition of the TYP. value is $T_A = 25^{\circ}C$



5. The smaller maximum transfer rate derived by using fMCK/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.4 V \leq EVDD0 < 3.3 V and 1.6 V \leq Vb \leq 2.0 V

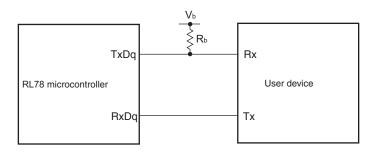
Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) = $\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- **6.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 5 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)





(2) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : ANI16 to ANI26

 $(T_{A} = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, 2.4 \text{ V} \le \text{AV}_{\text{REFP}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V},$ Reference voltage (+) = AV_{\text{REFP}}, Reference voltage (-) = AV_{\text{REFM}} = 0 \text{ V})

Parameter	Symbol	Conditior	าร	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	$\begin{array}{l} 10\text{-bit resolution} \\ EV_{DD0} \leq AV_{\text{REFP}} = V_{\text{DD}} ^{\text{Notes 3, 4}} \end{array}$	$\begin{array}{l} 2.4 \ V \leq AV_{REFP} \leq 5.5 \\ V \end{array}$		1.2	±5.0	LSB
Conversion time	t CONV	10-bit resolution	$3.6~V \leq V \text{DD} \leq 5.5~V$	2.125		39	μs
		Target pin : ANI16 to ANI26	$2.7~V \leq V \text{DD} \leq 5.5~V$	3.1875		39	μs
			$2.4~V \leq V \text{DD} \leq 5.5~V$	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	$\begin{array}{l} \mbox{10-bit resolution} \\ \mbox{EVDD0} \leq AV_{\text{REFP}} = V_{\text{DD}} ^{\text{Notes 3, 4}} \end{array}$	$\begin{array}{l} 2.4 \ V \leq AV_{\text{REFP}} \leq 5.5 \\ V \end{array}$			±0.35	%FSR
Full-scale error ^{Notes 1, 2}	Efs	$\begin{array}{l} \text{10-bit resolution} \\ \text{EVDD0} \leq AV_{\text{REFP}} = V_{\text{DD}} \\ \end{array} \end{array}$	$\begin{array}{l} 2.4 \ V \leq AV_{\text{REFP}} \leq 5.5 \\ V \end{array}$			±0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution $EVDD0 \leq AV_{REFP} = V_{DD}^{Notes 3, 4}$	$\begin{array}{l} 2.4 \ V \leq AV_{\text{REFP}} \leq 5.5 \\ V \end{array}$			±3.5	LSB
Differential linearity error	DLE	$\begin{array}{l} 10\text{-bit resolution} \\ EV \text{DD0} \leq AV_{\text{REFP}} = V_{\text{DD}} ^{\text{Notes 3, 4}} \end{array}$	$\begin{array}{l} 2.4 \ V \leq AV_{\text{REFP}} \leq 5.5 \\ V \end{array}$			±2.0	LSB
Analog input voltage	Vain	ANI16 to ANI26		0		AVREFP and EVDD0	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

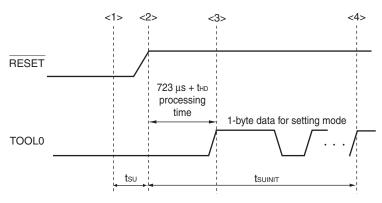
- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- When AV_{REFP} < V_{DD}, the MAX. values are as follows. Overall error: Add ±1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}. Zero-scale error/Full-scale error: Add ±0.05%FSR to the MAX. value when AV_{REFP} = V_{DD}. Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.
 When AV_{REFP} < EV_{DD0} ≤ V_{DD}, the MAX. values are as follows.
- 4. When AVREFP < EVDDD S VDD, the MAX. values are as follows. Overall error: Add ±4.0 LSB to the MAX. value when AVREFP = VDD. Zero-scale error/Full-scale error: Add ±0.20%FSR to the MAX. value when AVREFP = VDD. Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when AVREFP = VDD.



3.10 Timing of Entry to Flash Memory Programming Modes

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	tно	POR and LVD reset must be released before the external reset is released.	1			ms

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$



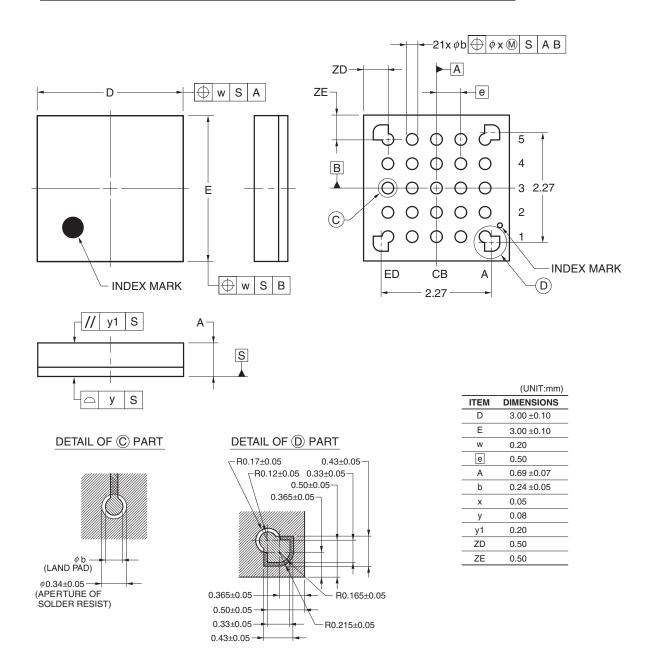
- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.
- **Remark** tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.
 - t_{SU} : Time to release the external reset after the TOOL0 pin is set to the low level
 - thd: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)



4.3 25-pin Products

R5F1008AALA, R5F1008CALA, R5F1008DALA, R5F1008EALA R5F1018AALA, R5F1018CALA, R5F1018DALA, R5F1018EALA R5F1008AGLA, R5F1008CGLA, R5F1008DGLA, R5F1008EGLA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA25-3x3-0.50	PWLG0025KA-A	P25FC-50-2N2-2	0.01



©2012 Renesas Electronics Corporation. All rights reserved.

